



概述

BIPN60050C 是比亚迪公司设计开发的智能功率模块 (IPM-Intelligent Power Module)。该产品具有封装小、抗干扰能力强等优点；实现了与绝缘栅双极型晶体管 (IGBT) 的最佳匹配。内部集成了欠压闭锁电路、过流保护电路和驱动电路，进一步提高了系统的可靠性。内置的高压集成电路 (HVIC) 提供了无需光耦隔离的驱动功能。由于采用了分立的负端子，可独立监测逆变器的每一相电流。该产品适用于结构紧凑、性能高效的交流电机驱动器，如小功率变频器、变频空调等领域。

General Description

BIPN60050C is an advanced intelligent power module that BYD has newly developed and designed to provide very compact and high performance as ac motor drivers mainly targeting low-power inverter-driven applications like air conditioner and washing machine. It combines optimized circuit protection and drive matched to low-loss IGBT. System reliability is further enhanced by the integrated under-voltage lock-out and Over-current protection. The high speed built-in HVIC provides opto-coupler-less single-supply IGBT gate driving capability that further reduce the overall size of the inverter system design. Each phase current of inverter can be monitored separately due to the divided negative dc terminals.

产品特性

- 采用陶瓷覆铜板 (DBC)，低热阻设计
- 600V、50A三相IGBT逆变器，内置门极驱动和功率器件保护用控制IC
- 分立的三相直流负端，可独立检测相电流
- 内置高压集成电路(HVIC)和自举二极管，可采用单电源驱动
- 绝缘等级为2500Vrms/min

Features

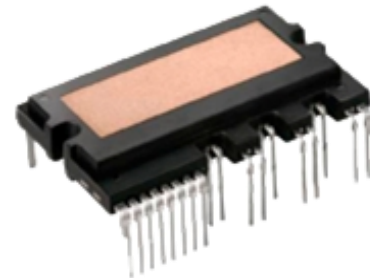
- Very low thermal resistance due to using DBC
- 600V50A Three-phase IGBT inverter bridge including control ICs for gate driving and protection
- Divided negative dc-link terminals for inverter current sensing applications
- Single-grounded power supply due to built-in HVIC and bootstrap diode
- Isolation rating of 2500Vrms/min

应用领域

- 空调、洗衣机等变频家电
- 小功率变频器
- 伺服控制系统
- 小功率交流电机传动系统使用的三相逆变器

Applications

- Three-phase inverter drive for small power ac motor control
- Home appliances applications like air conditioner and washing machine



封装/Package

DIP27-4426

典型应用电路/Typical Application Circuit

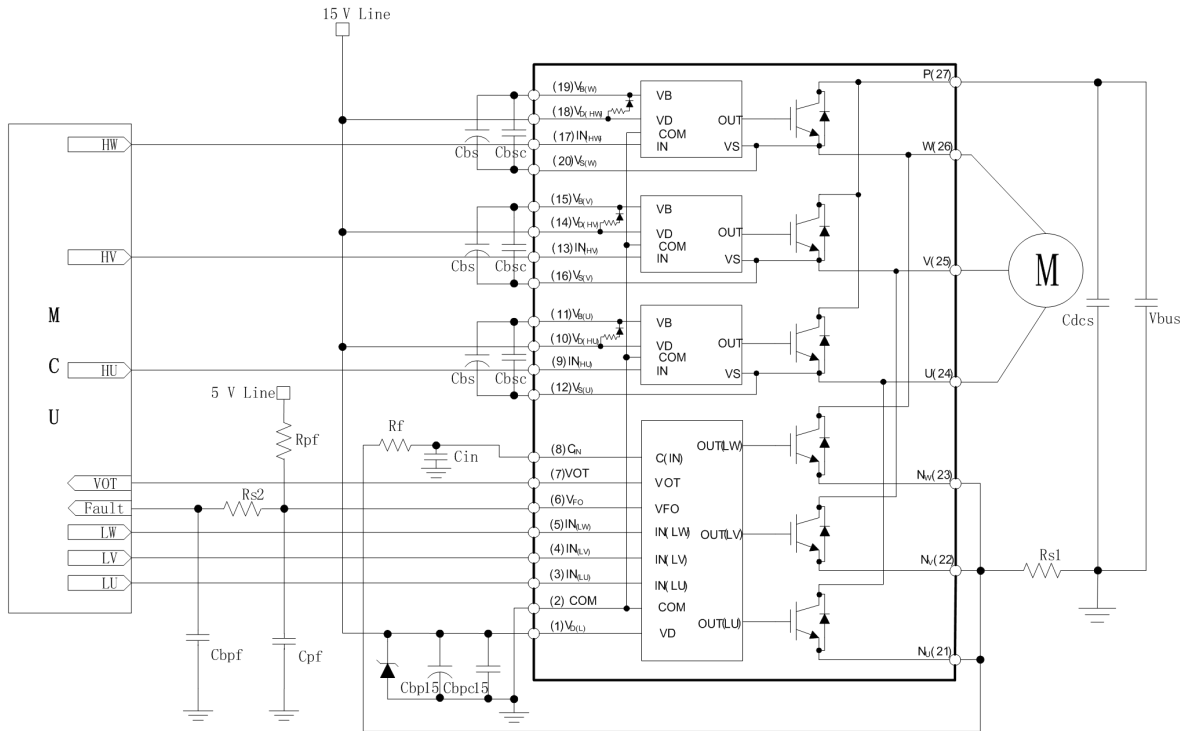


图 1. 典型应用电路
Fig 1. Typical Application Circuit

引脚布局/Pin Configuration

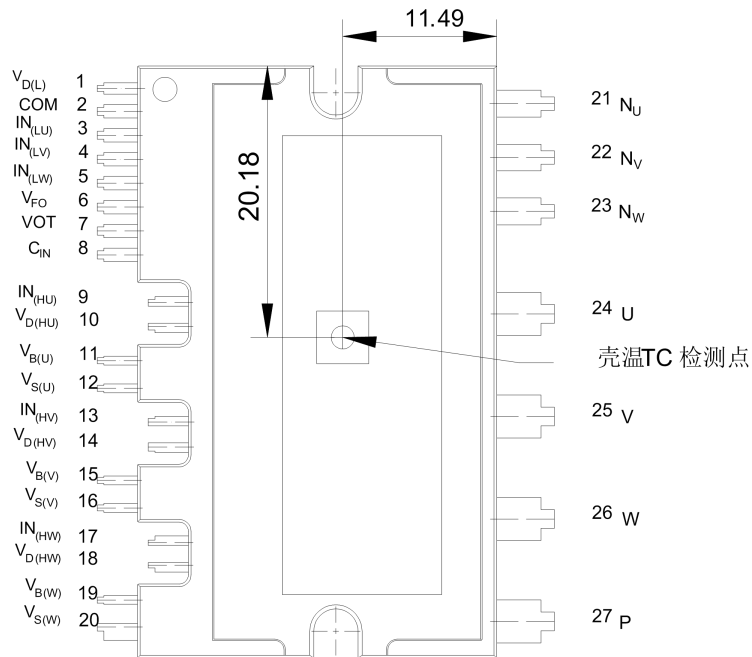


图 2. 引脚布局图(top view)
Fig 2. Pin Configuration(Top View)



引脚描述/Pin Descriptions

引脚号 Pin	引脚名 Name	描述 Descriptions
1	$V_{D(L)}$	低端 IGBT 驱动 IC 供电 Low-side common bias voltage for IC and IGBT driving
2	COM	电源（公共）地 Common supply ground
3	$IN_{(LU)}$	低端 U 相的信号输入 Signal input for low-side U phase
4	$IN_{(LV)}$	低端 V 相的信号输入 Signal input for low-side V phase
5	$IN_{(LW)}$	低端 W 相的信号输入 Signal input for low-side W phase
6	V_{FO}	故障输出 Fault output
7	V_{OT}	温度模拟输出 Voltage output of temperature
8	C_{IN}	短路电流检测输入端 Capacitor (low-pass Filter) for over-current detection input
9	$IN_{(HU)}$	高端 U 相的信号输入 Signal input for high-side U phase
10	$V_{D(HU)}$	高端 U 相 IGBT 驱动 IC 供电 High-side bias voltage for U phase IC
11	$V_{B(U)}$	高端 U 相 IGBT 驱动辅助供电正电源端 High-side bias voltage for U phase IGBT driving
12	$V_{S(U)}$	高端 U 相 IGBT 驱动辅助供电负电源端 High-side bias voltage ground for U phase IGBT driving
13	$IN_{(HV)}$	高端 V 相的信号输入 Signal input for high-side V phase
14	$V_{D(HV)}$	高端 V 相 IGBT 驱动 IC 供电 High-side bias voltage for V phase IC
15	$V_{B(V)}$	高端 V 相 IGBT 驱动辅助供电正电源端 High-side bias voltage for V phase IGBT driving
16	$V_{S(V)}$	高端 V 相 IGBT 驱动辅助供电负电源端 High-side bias voltage ground for V phase IGBT driving
17	$IN_{(HW)}$	高端 W 相的信号输入 Signal input for high-side W phase
18	$V_{D(HW)}$	高端 W 相 IGBT 驱动 IC 供电 High-side bias voltage for w phase IC
19	$V_{B(W)}$	高端 W 相 IGBT 驱动辅助供电正电源端 High-side bias voltage for w phase IC
20	$V_{S(W)}$	高端 W 相 IGBT 驱动辅助供电负电源端 High-side bias voltage ground for W phase IGBT driving
21	N_U	U 相的直流负端 Negative dc-link input for U phase



22	N _v	V 相的直流负端 Negative dc-link input for V phase
23	N _w	W 相的直流负端 Negative dc-link input for W phase
24	U	U 相输出 Output for U phase
25	V	V 相输出 Output for V phase
26	W	W 相输出 Output for W phase
27	P	直流正端 Positive dc-link input

最大绝对额定值/Absolute Maximum Ratings

(T_J=25°C,除非另外注明/unless otherwise noted)

逆变器部分/Inverter Part

符号 Symbol	参数 Parameter	工作条件 Conditions	额定值 Ratings	单位 Units
V _{PN}	电源电压 Supply voltage	施加在 P-N _U , N _v , N _w 之间 Applied between P-N _U , N _v , N _w	450	V
V _{PN(surge)}	电源 (浪涌) Supply voltage (surge)	施加在 P-N _U , N _v , N _w 之间 Applied between P-N _U , N _v , N _w	500	V
V _{CES}	集电极-发射极之间电压 Collector-emitter voltage	V _{GE} =0V, I _C =100μA, T _J =25°C	600	V
±I _C	单颗 IGBT 集电极电流 Each IGBT collector current	T _C = 25°C	50	A
±I _{CP}	单颗 IGBT 集电极电流 (峰值) Each IGBT collector current (peak)	T _C = 25°C, 持续 1ms 的脉冲宽度 T _C = 25°C, less than 1ms	100	A
P _C	集电极功耗 Collector dissipation	T _C = 25°C, 每一片 T _C = 25°C, per 1 chip	367	W
T _J	结温 Junction temperature	(注 1/Note 1)	-20~+150	°C

注 1: 智能功率模块中集成的功率芯片的最大结温额定值为 150°C (@T_C ≤ 100°C)。但是, 为了确保智能功率模块的安全工作, 平均结温应限制为 T_{J(ave)} ≤ 125°C (@T_C ≤ 100°C)。

Note 1: The maximum junction temperature rating of the power chips integrated within the IPM is 150°C (@ T_C ≤ 100°C). However, to ensure safe operation of the IPM, the average junction temperature should be limited to T_{J(ave)} ≤ 125°C (@ T_C ≤ 100°C).

控制部分/Control Part

符号 Symbol	参数 Parameter	工作条件 Conditions	额定值 Ratings	单位 Units
V _D	控制电源电压 Control supply voltage	施加在 V _{D(HU)} , V _{D(HV)} , V _{D(HW)} , V _{D(L)-COM} 之间 Applied between V _{D(HU)} , V _{D(HV)} , V _{D(HW)} , V _{D(L)-COM}	20	V
V _{DB}	高端控制辅助供电 Control supply	施加在 V _{B(U)-V_{S(U)}} , V _{B(V)-V_{S(V)}} , V _{B(W)-V_{S(W)}} 之 Applied between V _{B(U)-V_{S(U)}} , V _{B(V)-V_{S(V)}} , V _{B(W)-V_{S(W)}}	20	V



BIPN60050C

	voltage	间 Applied between $V_{B(U)}-V_{S(U)}$, $V_{B(V)}-V_{S(V)}$, $V_{B(W)}-V_{S(W)}$		
V_{IN}	输入电压 Input voltage	施加在 $IN_{(HU)}$, $IN_{(HV)}$, $IN_{(HW)}$, $IN_{(LU)}$, $IN_{(LV)}$, $IN_{(LW)}$ -COM 之间 Applied between $IN_{(HU)}$, $IN_{(HV)}$, $IN_{(HW)}$, $IN_{(LU)}$, $IN_{(LV)}$, $IN_{(LW)}$ -COM	-0.3~ V_D +0.3	V
V_{FO}	故障输出电压 Fault output voltage	施加在 V_{FO} -COM 之间 Applied between V_{FO} -COM	-0.3~ V_D +0.3	V
I_{FO}	故障输出电流 Fault output current	在引脚 V_{FO} 处灌电流 Sink current at V_{FO} terminal	5.0	mA
V_{CIN}	电流检测输入电压 Current sensing input voltage	施加在 C_{IN} -COM 之间 Applied between C_{IN} -COM	-0.3~ V_D +0.3	V

自举二极管部分/Bootstrap Diode Part

符号 Symbol	参数 Parameter	工作条件 Conditions	额定值 Ratings	单位 Units
V_{RRM}	最大重复反向电压 Maximum Repetitive Reverse Voltage		600	V
I_F	正向电流/Forward Current	$T_C = 25^\circ C$	1	A
I_{FP}	正向电流(脉冲) Forward Current (Peak)	$T_C = 25^\circ C$, 持续 1ms 的脉冲宽度 $T_C = 25^\circ C$, Under 1ms Pulse Width	2	A
T_J	结温/Junction temperature		-20~+150	$^\circ C$

整个系统/Total System

符号 Symbol	参数 Parameter	工作条件 Conditions	额定值 Ratings	单位 Units
$V_{PN(Prot)}$	自保护电源电压限制 (短路保护能 力) Self protection supply voltage limit (short circuit protection capability)	$V_D = 13.5\sim 16.5V$, $T_J = 125^\circ C$, 非 重复性, 小于 $5\mu s$ $V_D = 13.5\sim 16.5V$, inverter part $T_J =$ $125^\circ C$, non-repetitive, less than $5\mu s$	400	V
T_C	模块壳体工作温度 Module case operation temperature	$-20^\circ C \leq T_J \leq 125^\circ C$, 图 2 (Fig 2.)	-20~+100	$^\circ C$
T_{STG}	存储/保存温度 Storage temperature		-40~+125	$^\circ C$
V_{ISO}	绝缘电压/Isolation voltage	60Hz, 正弦波形, 交流 1 分钟, 所 有引脚与 DBC 之间 60Hz, sinusoidal, AC 1 minute, connection pins to heat sink plate	2500	Vrms

热阻/Thermal Resistance

符号 Symbol	参数 Parameter	工作条件 Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Units
$R_{th(j-c)Q}$	结点-壳体的热阻 Junction to case	逆变器 IGBT 部分 (每 1/6 模块) Inverter IGBT part (per 1/6 module)	-	-	0.34	$^\circ C/W$



$R_{th(j-c)F}$	thermal resistance	逆变器 FRD 部分 (每 1/6 模块) Inverter FRD part (per 1/6 module)	-	-	0.64	$^{\circ}C/W$
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电气特性/Electrical Characteristics

($T_J=25^{\circ}C$,除非另外注明/unless otherwise noted)

逆变器部分/Inverter Part

符号 Symbol	参数说明 Parameter	工作条件 Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Units
$V_{CE(SAT)}$	集电极-发射极间饱和电压 Collector-emitter saturation voltage	$V_D=V_{BS}=15V, V_{IN}=5V,$ $I_C=50A, T_J=25^{\circ}C$	---	1.8	2.2	V
V_F	FRD 正向电压 FRD forward voltage	$V_{IN}=0V, I_C=30A, T_J=25^{\circ}C$	---	1.7	2.35	
高端	t_{ON}	开通时间 Turn-on time	---	900	---	ns
	$t_{C(ON)}$	开通交叉时间 Turn-on across time	---	500	---	ns
	t_{OFF}	关断时间 Turn-off time	---	1050	---	ns
	$t_{C(OFF)}$	关断交叉时间 Turn-off across time	$V_{PN}=300V,$ $V_D=V_{BS}=15V, I_C=50A,$ $V_{IN}=0\sim 5V, T_J=25^{\circ}C,$ 感性负载 (注 2) Inductive load (Note 2)	---	200	---
低端	t_{ON}	开通时间 Turn-on time	---	900	---	ns
	$t_{C(ON)}$	开通交叉时间 Turn-on across time	---	660	---	ns
	t_{OFF}	关断时间 Turn-off time	---	1100	---	ns
	$t_{C(OFF)}$	关断交叉时间 Turn-off across time	---	240	---	ns
I_{CES}	集电极-发射极间漏电流 Collector-Emitter leakage current	$V_{CE}=V_{CES}, V_{GE}=0V,$ $T_J=25^{\circ}C$	---	---	0.1	mA

注 2: t_{ON} 和 t_{OFF} 包括模块内部驱动集成电路(IC) 的传输延迟时间。 $t_{C(ON)}$ 和 $t_{C(OFF)}$ 指在内部给定的门极驱动条件下, IGBT 本身的切换时间。详细信息, 参考图 3。

Note 2 : t_{on} and t_{off} include the propagation delay time of the internal drive IC. $t_{c(on)}$ and $t_{c(off)}$ are the switching time of IGBT itself under the given gate driving condition internally. See figure 3.

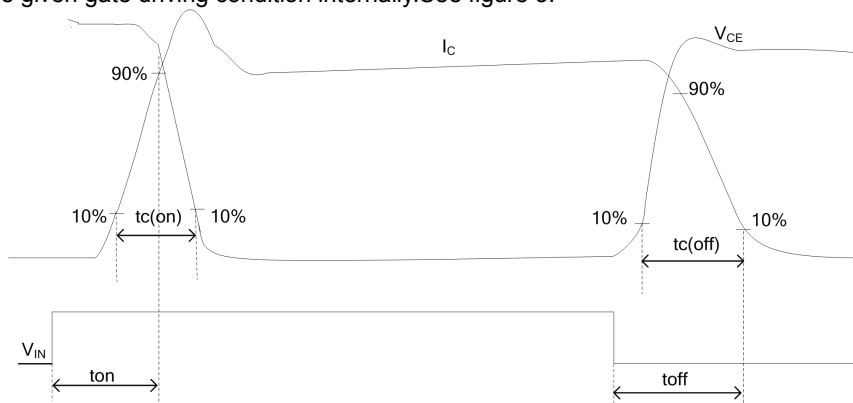


图 3.开关时间定义
Fig 3. Switching Time Definition



控制部分/Control Part

符号 Symbol	参数 Parameter	工作条件 Conditions		最小值 Min.	典型值 Typ.	最大值 Max.	单位 Units
I_{DL}	V_D 静态电流 Quiescent V_D	$V_D=15V$, $I_{N(LU,LV,LW)}=0V$	$V_{D(L)}-COM$	---	---	600	μA
I_{DH}	supply current	$V_D=15V$, $I_{N(HU,HV,HW)}=0V$	$V_{D(HU)}, V_{D(HV)}$, $V_{D(HW)}-COM$	---	---	300	μA
I_{QBS}	V_{BS} 静态电流 Quiescent V_{BS} supply current	$V_{BS}=15V$, $I_{N(HU,HV,HW)}=0V$	$V_{B(U)}-V_{S(U)}$, $V_{B(V)}-V_{S(V)}$, $V_{B(W)}-V_{S(W)}$	---	---	150	
V_{FOH}	故障输出电压 Fault output voltage	$V_{CIN}=0V$, V_{FO} 电路 4.7K 上拉到 5V V_{FO} circuit: 4.7K to 5V pull-up		4.5	---	---	V
V_{FOL}		$V_{CIN}=1V$, V_{FO} 电路 4.7K 上拉到 5V V_{FO} circuit: 4.7K to 5V pull-up		---	---	0.8	
$V_{CIN(ref)}$	短路保护触发 电压 Short circuit trip level	$T_C=-20\sim 100^\circ C$, $V_D=15V$ (注 3 / Note3)		0.44	0.51	0.56	
UV_{DLD}	供电电路欠压 保护 Supply circuit under-voltage protection	检测电平 (低端) Detection level (LS)		11.0	12.0	13.0	V
UV_{DLR}		复位电平 (低端) Rest level (LS)		12.0	13.0	14.0	
UV_{BSD}		检测电平 (高端) Detection level (HS)		9.0	10.0	11.0	
UV_{BSR}		复位电平 (高端) Rest level (HS)		10.0	11.0	12.0	
t_{FO}	故障信号输出 脉冲宽度 Fault-out pulse width	供电电路欠压保护或短路保护 Supply circuit under-voltage protection or Short circuit protection		50	---	---	μs
$V_{IN(ON)}$	导通阈值电压 ON threshold voltage	施加在 $I_{N(HU)}, I_{N(HV)}, I_{N(HW)}, I_{N(LU)}$, $I_{N(LV)}, I_{N(LW)}-COM$ 之间		---	---	3.0	V
$V_{IN(OFF)}$	关断阈值电压 OFF threshold voltage	Applied between $I_{N(HU)}, I_{N(HV)}, I_{N(HW)}$, $I_{N(LU)}, I_{N(LV)}, I_{N(LW)}-COM$		0.8	---	---	

注 3 : 只有下桥驱动具有短路保护功能。

Note 3 : Short circuit protection is functioning only at the low-side.

自举二极管部分/Bootstrap Diode Part

符号 Symbol	参数 Parameter	工作条件 Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Units
V_F	正向电压 Forward Voltage	$I_F = 1A, T_J = 25^\circ C$	---	24.7	---	V
t_{rr}	反向恢复时间 Reverse Recovery Time	$I_F = 1A, T_J = 25^\circ C$	---	130	---	ns

机械特性和额定值/Mechanical Characteristics and Ratings

符号 Symbol	工作条件 Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Units
安装扭矩 Mounting torque	安装螺钉: -M3, 螺钉 结构参见图 5 Mounting screw: - M3, see figure 5 for screw structure. 推荐选用: 0.62N·m Recommended 0.62N.m	0.51	0.62	0.72	N·m
重量 Weight		---	15	---	g
器件平面度 Device flatness	参见图 4 (See Fig 4)	0	---	120	um

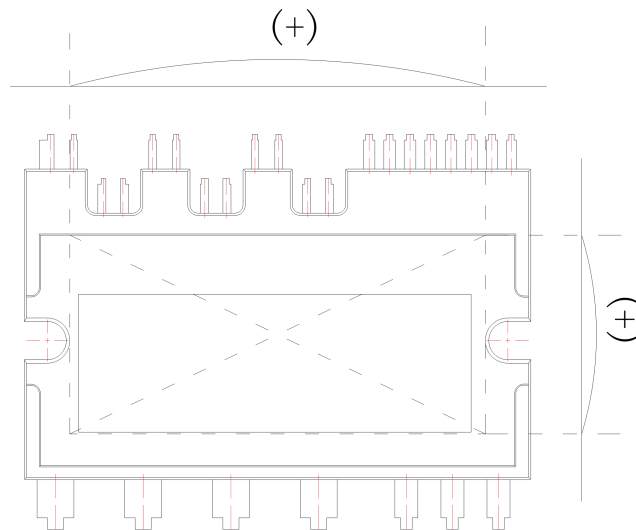


图 4. 平面度测量位置
Fig 4. Flatness Measurement Position

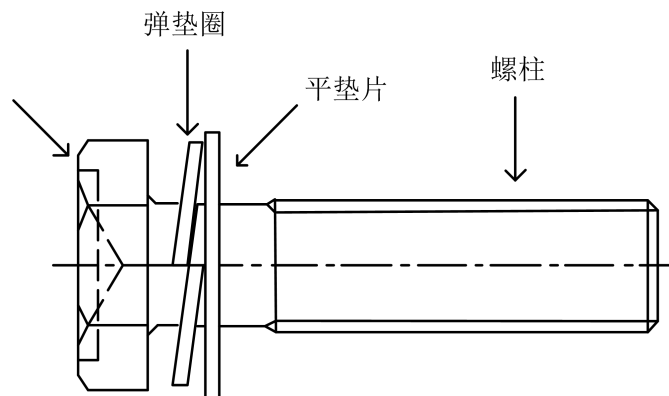


图 5. 螺钉结构图
Fig 5. screw structure diagram



推荐工作条件/Recommended Operating Conditions

符号 Symbol	参数 Parameter	工作条件 Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Units
V_{PN}	电源电压 Supply voltage	施加在 P-N _U , N _V , N _W 之间 Applied between P -N _U , N _V , N _W	---	300	400	V
V_D	控制电源电压 Control supply voltage	施加在 V _{D(HU)} , V _{D(HV)} , V _{D(HW)} , V _{D(L)} -COM 之间 Applied between V _{D(HU)} , V _{D(HV)} , V _{D(HW)} , V _{D(L)} -COM	13.5	15.0	16.5	
V_{BS}	高端辅助供电 High-side bias voltage	施加在 V _{B(U)} -V _{S(U)} , V _{B(V)} -V _{S(V)} , V _{B(W)} -V _{S(W)} 之间 Applied between V _{B(U)} -V _{S(U)} , V _{B(V)} - V _{S(V)} , V _{B(W)} -V _{S(W)}	13.5	15.0	18.5	
ΔV_D , ΔV_{DB}	控制电源电压波动 Control supply variation		-1	---	1	V/ μ s
t_{DEAD}	防止桥臂直通的死区时间 Blanking time for preventing arm-short	适用于每个输入信号 For each input signal	2.0	---	---	μ s
f_{PWM}	PWM 输入信号 PWM input signal	-20°C ≤ T _C ≤ 100°C, -20°C ≤ T _J ≤ 125°C	---	---	20	kHz
V_{SEN}	电流检测产生的电压 Voltage for current sensing	施加在 N _U , N _V , N _W - COM 之间 (包括浪涌电压) Applied between N _U , N _V , N _W -COM (Including surge voltage)	-4	---	4	V

IPM 保护功能时序图/Time charts of IPM Protection Function

过流保护/Over Current Protection

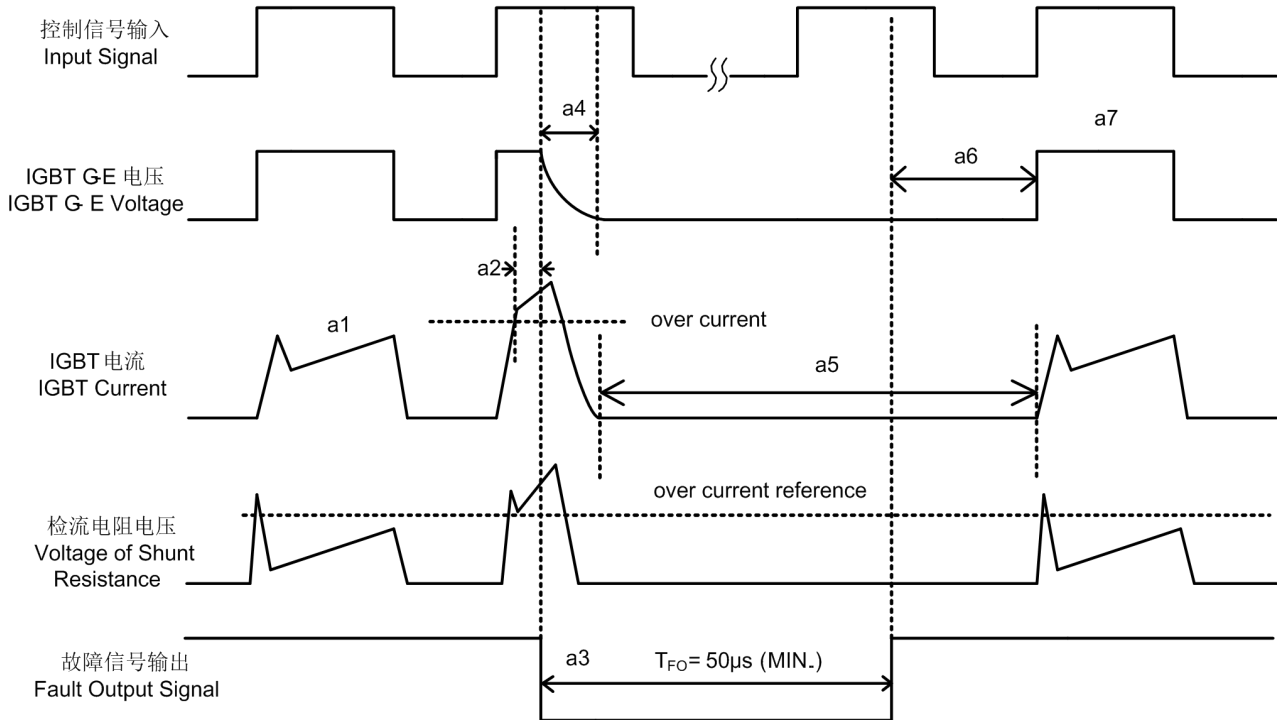


图 6.过流保护

Fig 5.Over Current Protection

(仅下桥有,包含外部分流电阻和 RC 滤波器)

Low-side only ,with the external shunt resistance and RC filter)

a1 IGBT正常工作, 输出电流

Normal operation: IGBT ON and carrying current

a2 短路电流检测及滤波

Over current detection and filter

a3 故障信号输出开始, 脉宽由外部 C_{FO} 电容调节

Fault output timer operation starts: The pulse width of the V_{FO} is set by the external capacitor C_{FO}

a4 IGBT关断

IGBT turns off

a5 IGBT处于关断状态

IGBT OFF state

a6 故障信号输出恢复高电平, 但IGBT在下一个高电平输入信号时才会开通

V_{FO} finishes output, but IGBTs don't turn on until inputting next ON signal.

a7 当输入信号由L→H时, IGBT正常工作

Normal operation: IGBT ON and outputs current by next ON signal(L→H).

下桥欠压保护/Under-Voltage Protection of Low-side

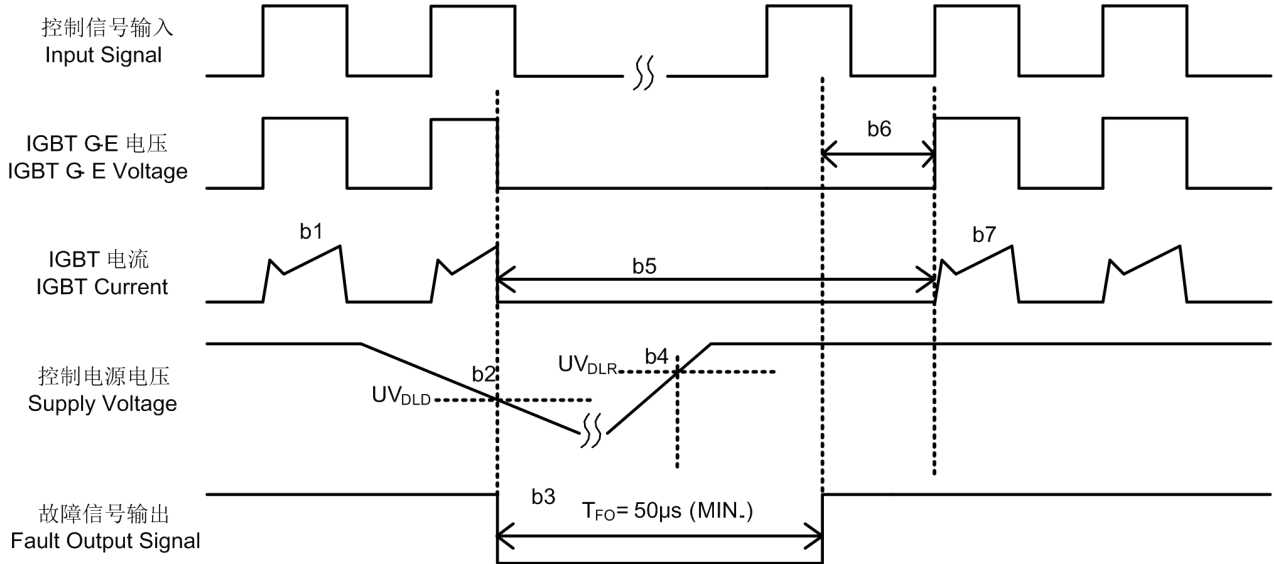


图 7. 下桥欠压保护

Fig 6. Under-Voltage Protection of Low-side

- b1 IGBT正常工作，输出电流
Normal operation: IGBT ON and carrying current
- b2 欠压保护检测 (UV_{DLD})
Under voltage detection (UV_{DLD})
- b3 故障信号输出低电平
Fault output timer operation starts:
- b4 欠压恢复 (UV_{DLR})
Under voltage reset (UV_{DLR})
- b5 IGBT处于关断状态
IGBT OFF state
- b6 故障信号输出恢复高电平，但IGBT在下一个高电平输入信号时才会开通
 V_{FO} finishes output, but IGBTs don't turn on until inputting next ON signal.
- b7 当输入信号由L→H时，IGBT正常工作
Normal operation: IGBT ON and outputs current by next ON signal(L→H).

上桥欠压保护/Under-Voltage Protection of High-side

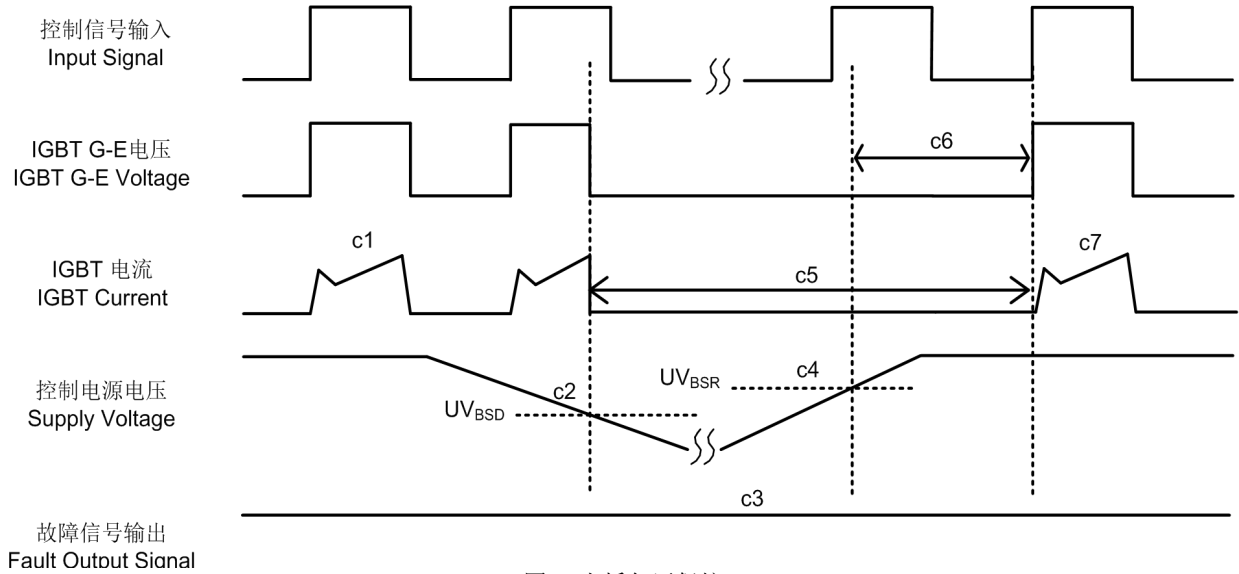


图 8.上桥欠压保护

Fig 7.Under-Voltage Protection of High-side

- c1 IGBT正常工作，输出电流
Normal operation: IGBT ON and carrying current
- c2 欠压保护检测 (UV_{BSD})
Under voltage detection (UV_{BSD})
- c3 故障信号保持高电平，上桥欠压无故障信号输出
No fault output signal
- c4 欠压恢复 (UV_{BSR})
Under voltage reset (UV_{BSR})
- c5 IGBT处于关断状态
IGBT OFF state
- c6 欠压已恢复，但IGBT在下一个高电平输入信号时才会开通
Under voltage reset, but IGBTs don't turn on until inputting next ON signal.
- c7 当输入信号由L→H时，IGBT正常工作
Normal operation: IGBT ON and outputs current by next ON signal(L→H).

内部等效电路和输入输出引脚/Internal Equivalent Circuit and Input/Output Pins

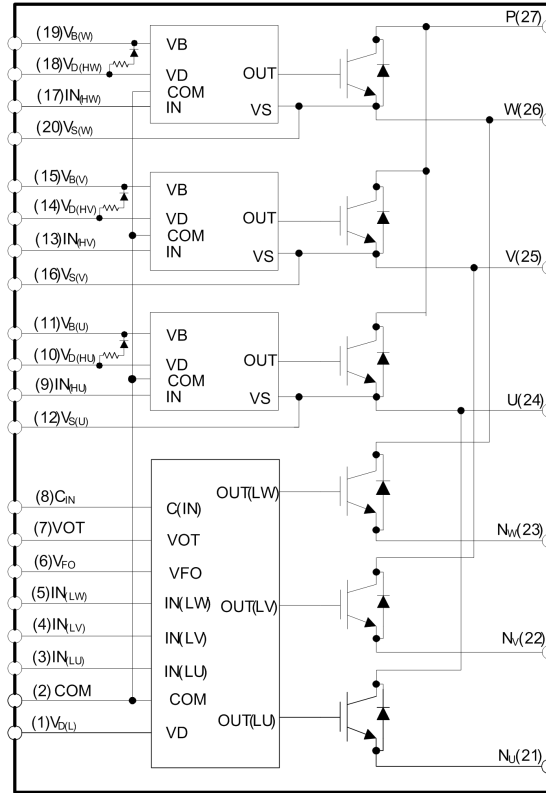


图9. 内部等效电路和输入输出引脚
Fig 8. Internal Equivalent Circuit and Input/Output Pins

注:

1. 逆变器低端由三个 IGBT 组成，每个 IGBT 配有一个快恢复二极管(FRD)并包括一个具有门极驱动和保护功能的控制集成电路(LVIC)。
2. 逆变器的功率端是由逆变器的四个直流端和逆变器的三个输出端组成。
3. 逆变器高端由三个 IGBT 组成，每个 IGBT 配有一个快恢复二极管(FRD),一个驱动集成电路(HVIC)和一个自举二极管(bootstrap diode)。

Note:

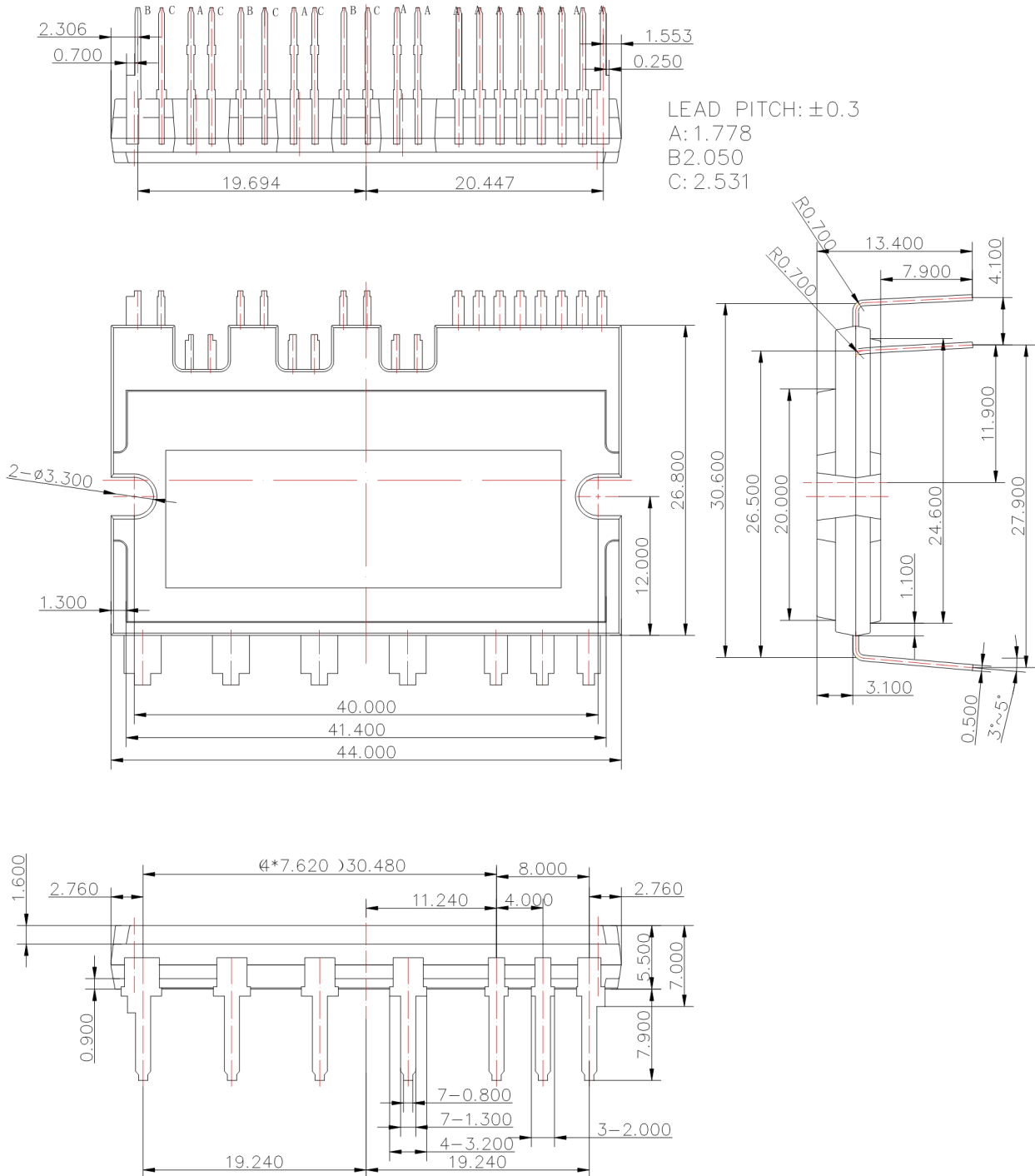
1. Inverter low-side is composed of three IGBTs, freewheeling diodes for each IGBT and one control IC. It has gate drive and protection functions
2. Inverter power side is composed of four inverter dc-link input terminals and three inverter output terminals
3. Inverter high-side is composed of three IGBTs, freewheeling diodes, bootstrap diodes and three drive ICs for each IGBT



封装轮廓详图/Detailed Package Outline Drawings

封装/Package: DIP27-4426

(单位/Unit: mm)



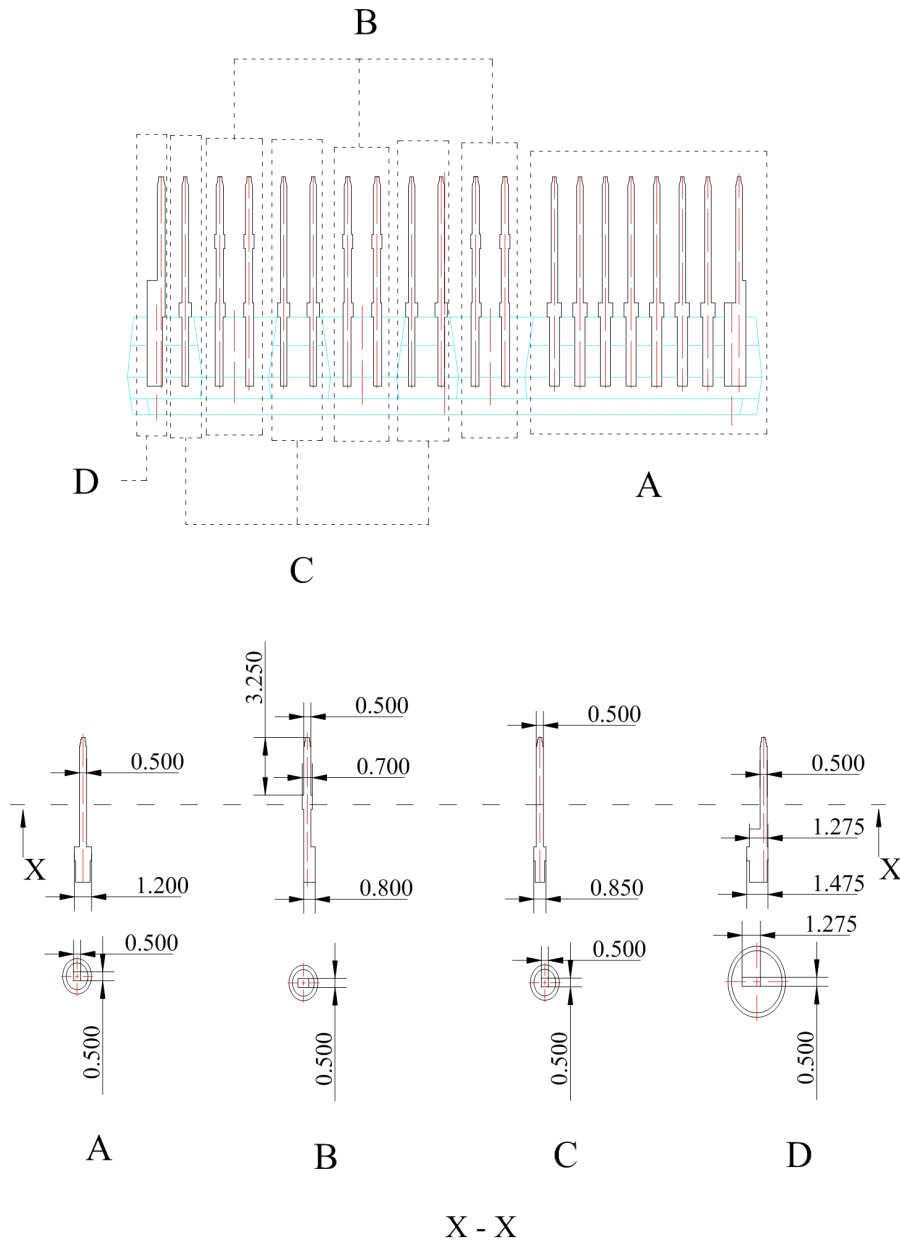


图 10. 封装轮廓详图
Fig 9. Detailed Package Outline Drawings

包装/Packing

包装 package	pcs/料管 pcs/tube	料管/内盒 tube/ inner box	内盒/箱 inner box/ carton	pcs/箱 pcs/carton
料管/tube	10	7	5	350



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